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(12) **United States Design Patent**
Sawada

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(54) **POWER SEMICONDUCTOR MODULE**

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(**) Term: **15 Years**

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Related U.S. Application Data

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(30) **Foreign Application Priority Data**

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(51) **LOC (12) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**

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361/679.01, 713, 728, 736, 760, 761, 772,
361/775, 783, 820; 174/250, 523;
438/15, 25, 26, 51, 55, 63, 64, 106
CPC . H01L 21/00; H01L 2224/42; H01L 2224/43;
H01L 2021/00; H01L 2021/02; H01L
2021/04; H01L 21/4814; H01L 21/4846;
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2224/08054; H01L 23/58; H05B 41/14;

H02B 6/4201; G02B 6/4256; G02B
6/4257; G02B 6/4261; G02B 6/4262;
G02B 6/428; G02B 6/4281; H05K 1/14;
H05K 1/141; H05K 1/142; H05K 1/144;
H05K 1/18; H05K 1/181; H05K 1/182;
H05K 1/026

See application file for complete search history.

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(57) **CLAIM**

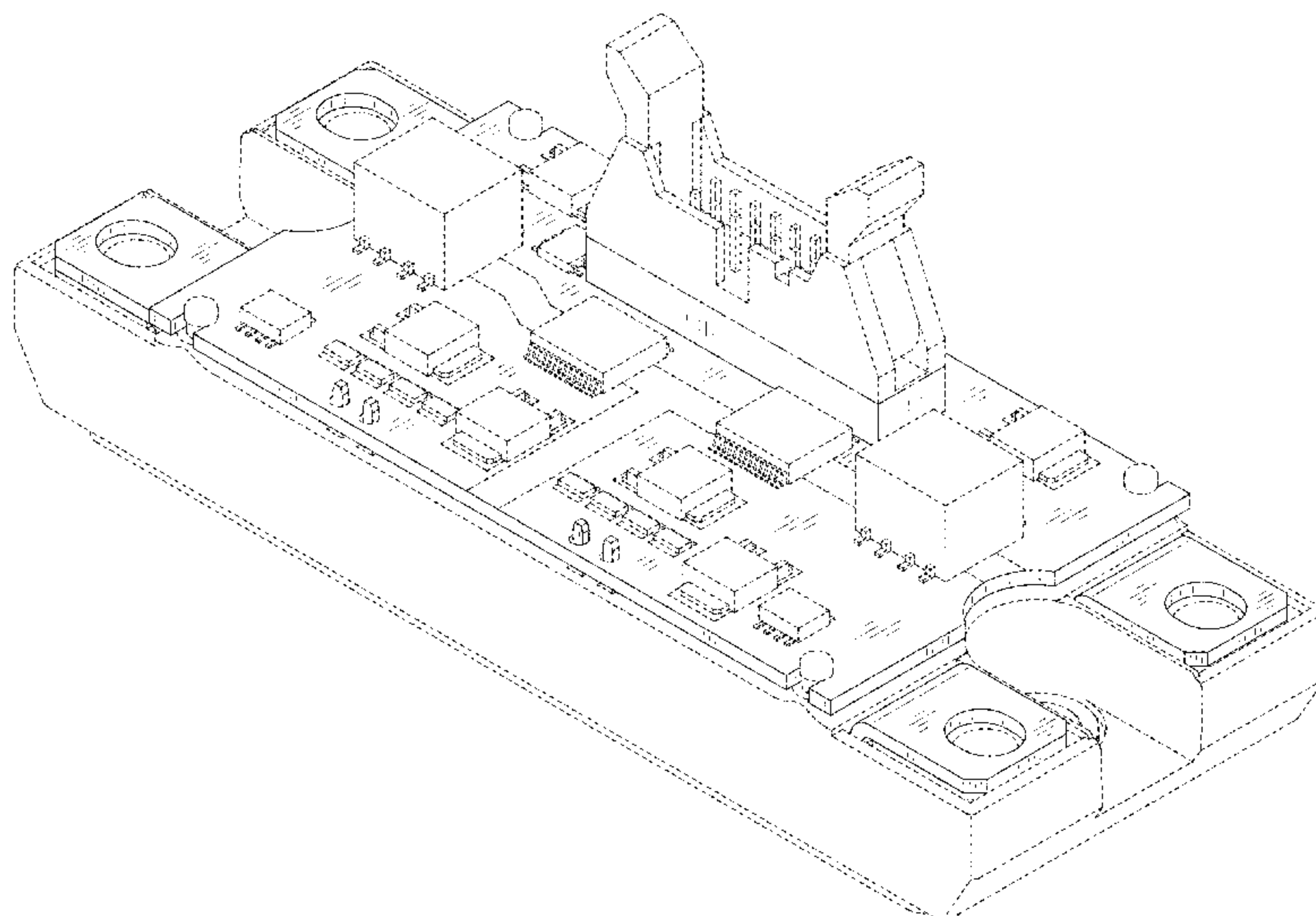
The ornamental design for a power semiconductor module,
as shown and described.

DESCRIPTION

FIG. 1 is a front, top, and right side perspective view of a
power semiconductor module, showing my new design;
FIG. 2 is a front view thereof;
FIG. 3 is a rear view thereof;
FIG. 4 is a top plan view thereof;
FIG. 5 is a right side view thereof; and,
FIG. 6 is a left side view thereof.

The features shown in broken lines in the drawings depict
portions of the article that form no part of the claimed
design. The dash-dotted lines denote the boundary of the
claim and form no part of the claimed design.

1 Claim, 6 Drawing Sheets



(56)

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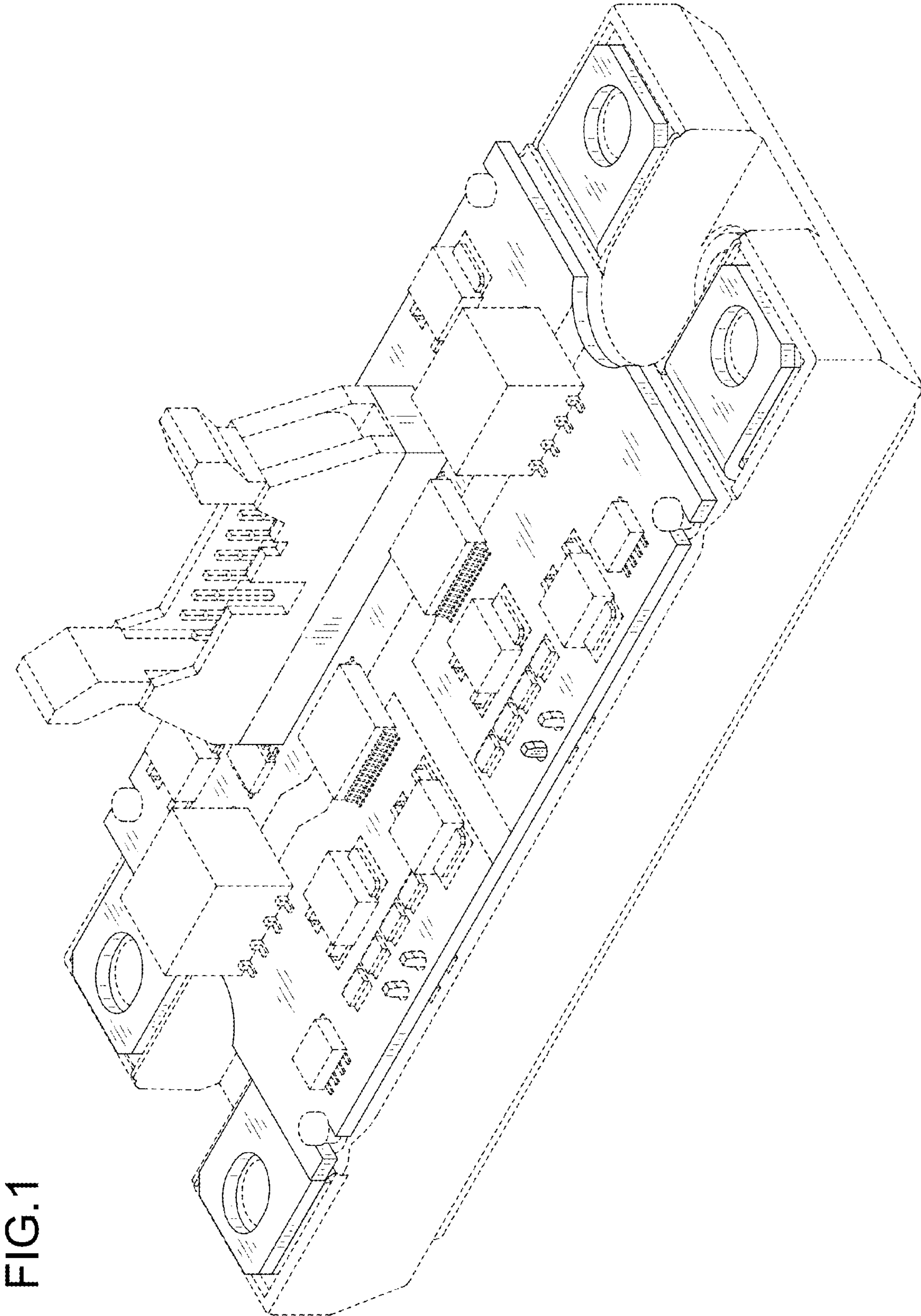


FIG.1

FIG.2

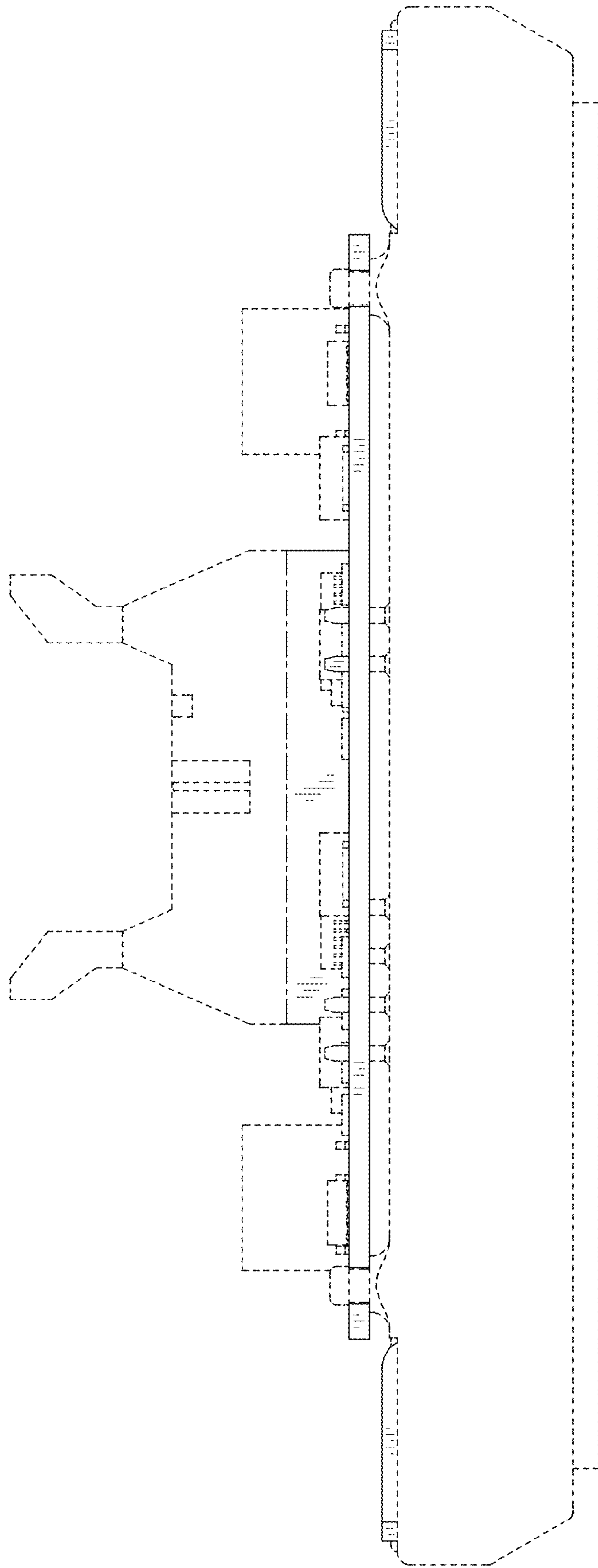
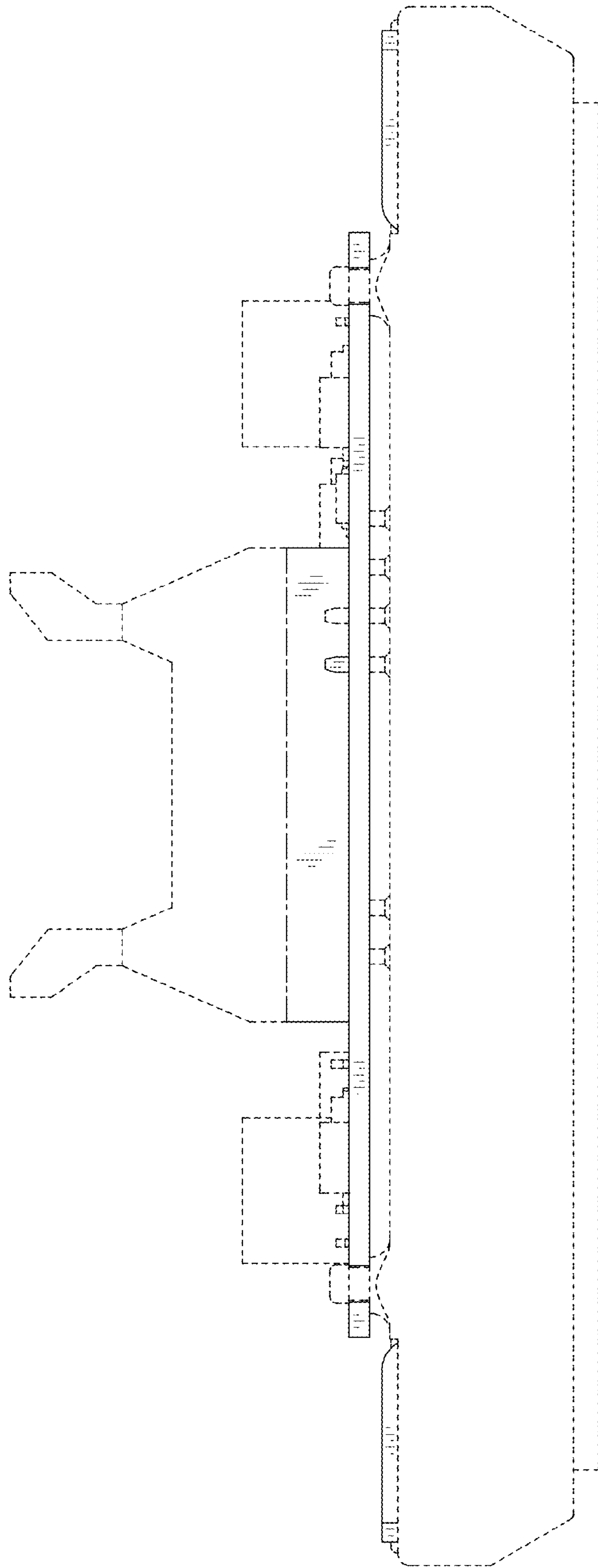


FIG.3



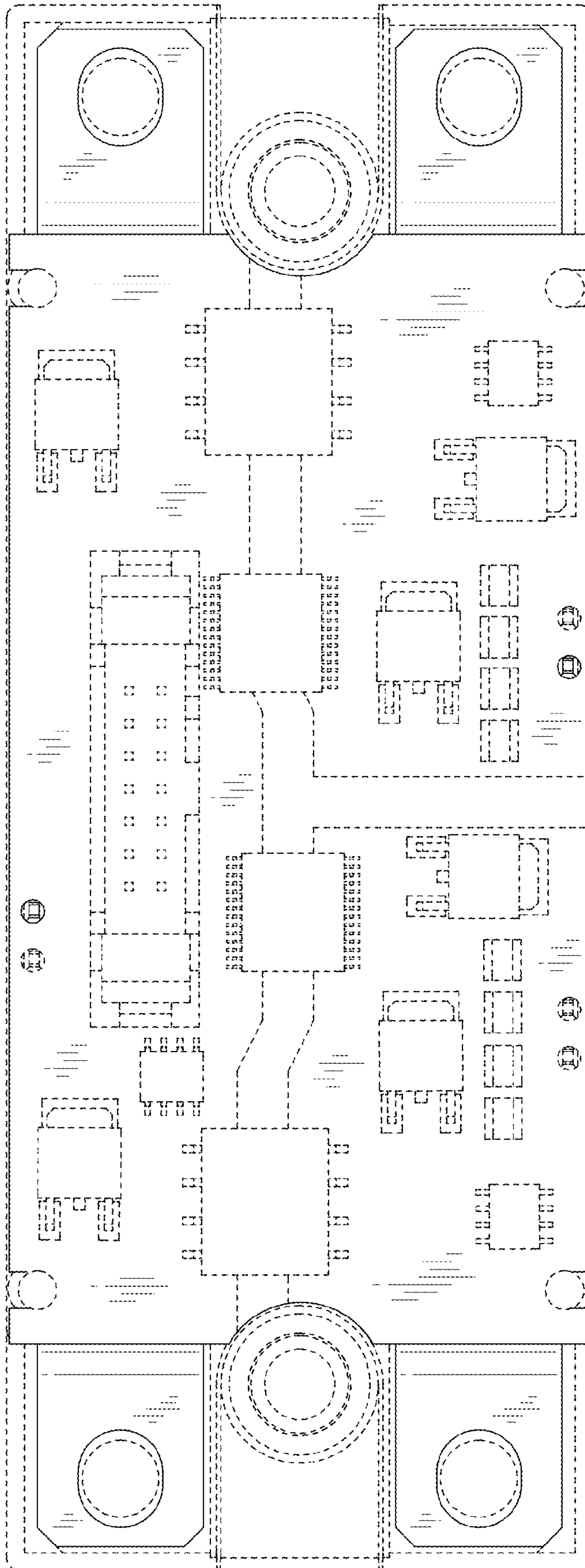


FIG.4

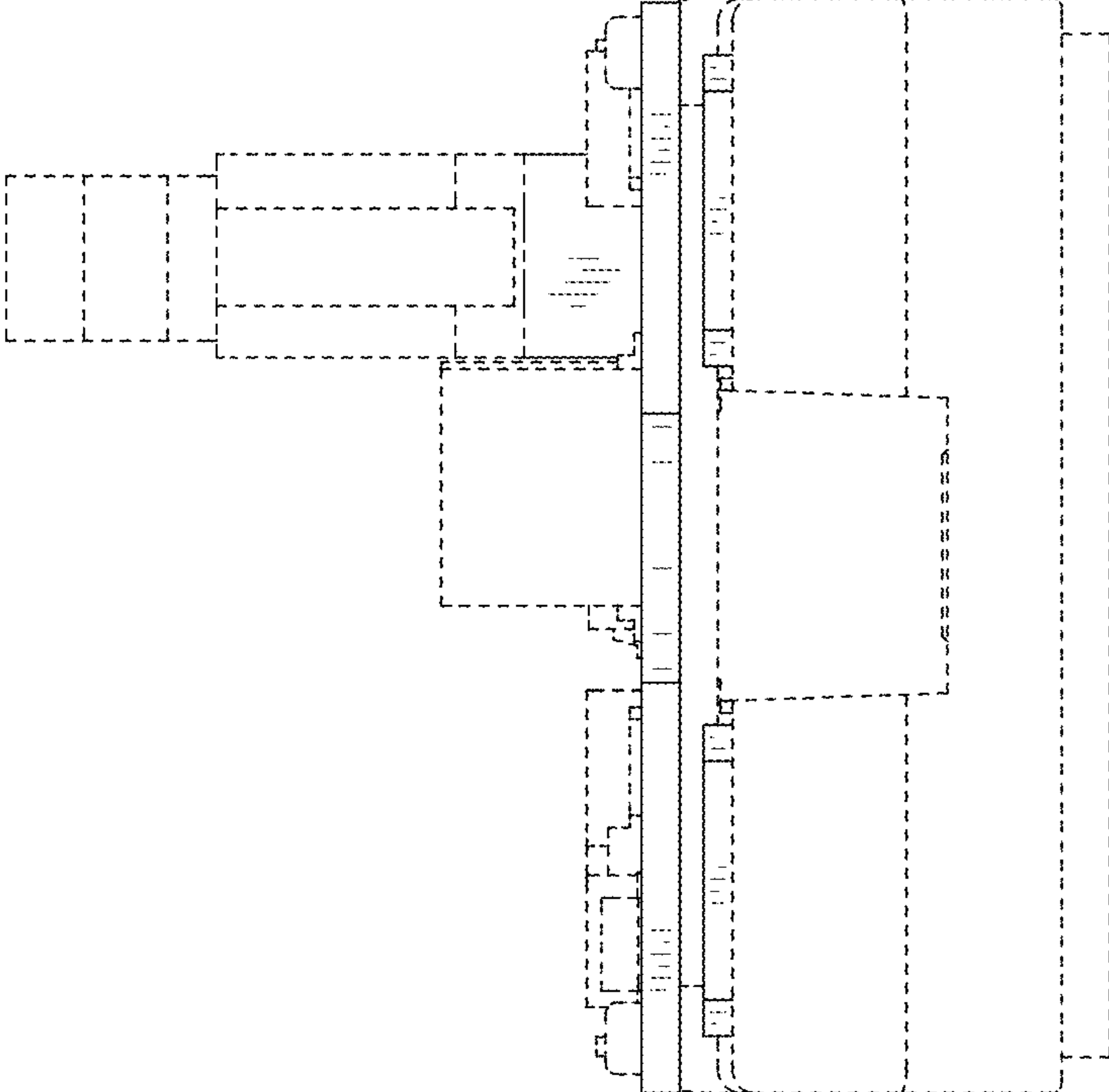


FIG.5

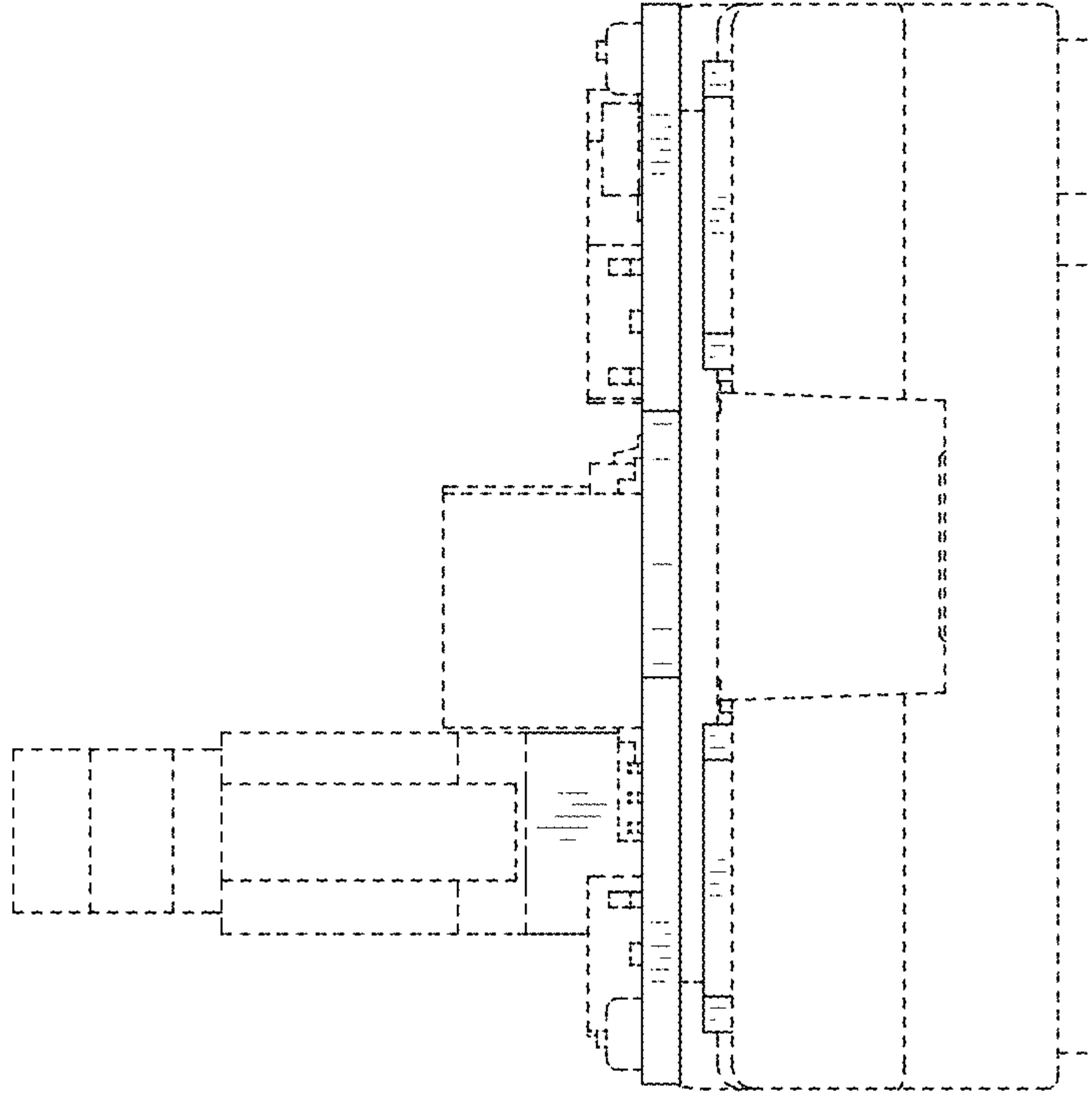


FIG.6